

Low-Voltage, 0.45-Ω, SPDT Analog Switch

DESCRIPTION

The DG2717 is a low voltage, low on resistance, single-pole/double-throw (SPDT) monolithic CMOS analog switch designed for high performance switching of analog signals. Combining low-power, high speed, low on-resistance, and small package size, the DG2717 is ideal for portable and battery power applications.

The DG2717 has an operation range from 1.6 V to 4.3 V single supply, and is low voltage logic compatible within this range, allowing the easy interface with low voltage DSP or MCU control logic. These traits make it ideal for one cell Li-ion battery direct power.

The switch conducts signals within power rails equally well in both directions when on, and blocks up to the power supply level when off. Break-before-make is guaranteed.

The DG2717 is built on Vishay Siliconix's sub micron CMOS low voltage process.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with lead (Pb)-free device terminations. For analog switching products manufactured in SC89 package, the lead (Pb)-free "E3" suffix is being used as a designator. It has a Tin device termination that meets all JEDEC standards for reflow and MSL rating.

FEATURES

- Low Voltage Operation (1.6 V to 4.3 V)
- Low On-Resistance r_{DS(on)}: 0.45 Ω Typ.
- Fast Switching t_{ON}: 22 ns, t_{OFF}: 8 ns
- · Low Leakage
- TTL/CMOS Compatible
- SC-89 (1.6 mm x 1.6 mm) Package

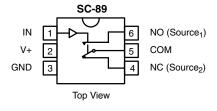
BENEFITS

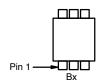
- Reduced Power Consumption
- Simple Logic Interface
- High Accuracy
- Reduce Board Space

APPLICATIONS

- · Cellular Phones
- PMP/MP3
- · Audio and Video Signal Routing
- Power Switch
- · Reed Relay Replacement

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





Device Marking: Bx x = Date/Lot Traceability Code

TRUTH TABLE				
Logic	NC	NO		
0	ON	OFF		
1	OFF	ON		

ORDERING INFORMATION					
Temp Range	Package	Part Number			
- 40 to 85 °C	SC89-6	DG2717DX-T1-E3			

DG2717

Vishay Siliconix



ABSOLUTE MAXIMUM RATINGS					
Parameter		Limit	Unit		
Reference V+ to GND	- 0.3 to + 5.0	V			
IN, COM, NC, NO ^a	- 0.3 to (V+ + 0.3)				
Continuous Current (NO, NC and COM P	± 200	mA			
Peak Current (Pulsed at 1 ms, 10 % duty cycle)		± 300	- IIIA		
Storage Temperature (D Suffix)		- 65 to 150	°C		
Power Dissipation (Packages) ^b	6-Pin SC89	172	mW		

Notes:

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC Board.
- c. Derate 2.15 mW/°C above 70 °C.

SPECIFICATIONS (V	/+ = 1.8 V						
		Test Condition Otherwise Unless Specified		Limits - 40 to 85 °C		С	
Parameter	Symbol	$V+ = 1.8 \text{ V}, \pm 10 \%, V_{IN} = 0.4 \text{ or } 1.0 \text{ V}^{e}$	Temp ^a	Min ^b	Typ ^c	Max ^b	Unit
Analog Switch							
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}		Full	0		V+	V
On-Resistance	r _{ON}	V+ = 1.8 V, V _{COM} = 0.2 V, I _{NO/NC} = 100 mA	Room Full		1.0	2.0 2.1	Ω
Digital Control							
Input High Voltage	V _{INH}		Full	1.0			V
Input Low Voltage	V _{INL}		Full			0.4	v
Input Capacitance ^d	C _{in}		Full		7		pF
Input Current ^f	I _{INL} or I _{INH}	V _{IN} = 0 V or V+	Full	- 1		1	μΑ
Dynamic Characteristics							
Turn-On Time ^d	t _{ON}	V_{NO} or V_{NC} = 1.5 V, R_L = 50 Ω , C_L = 35 pF Figures 1 and 2	Room Full ^d		54	74 81	
Turn-Off Time ^d	t _{OFF}		Room Full ^d		14	34 35	ns
Break-Before-Make Time ^d	t _d		Room	8			
Charge Injection ^d	Q _{INJ}	$C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN} = 0 \Omega, \text{ Figure 3}$	Room		26		рC
Off-Isolation ^d	O _{IRR}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room		- 54		ı.
Crosstalk ^d	X _{TALK}		Room		- 60		dB
NO, NC Off Capacitance ^d	C _{NO(off)} , C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		80		pF
Channel-On Capacitanced	C _{ON}		Room		180		





SPECIFICATIONS (V	Test Condition			Limits			
Parameter		Otherwise Unless Specified		ı	40 to 85 °	C	
	Symbol	$V+ = 2.7 V \text{ to } 3.6 V, V_{IN} = 0.5 \text{ or } 1.4 V^{e}$	Temp ^a	Min ^b	Тур ^с	Max ^b	Unit
Analog Switch							
Analog Signal Range ^d	V_{NO}, V_{NC}, V_{COM}		Full	0		V+	V
0.5	_	V+ = 2.7 V, V _{COM} = 1.5 V I _{NO} , I _{NC} = 100 mA	Room Full		0.5	0.7 0.8	
On-Resistance	r _{ON}	$V+ = 3.6 \text{ V}, V_{COM} = 0.5 \text{ V}, 2.0 \text{ V}$ $I_{NO}, I_{NC} = 100 \text{ mA}$	Room Full		0.45	0.65 0.75	Ω
r _{ON} Flatness ^d	r _{ON} Flatness	V+ = 2.7 V, V _{COM} = 0.6 V, 2.1 V I _{NO} , I _{NC} = 100 mA	Room			0.2	
r _{ON} Match ^d	Δr _{ON}	V+ = 2.7 V, V _{COM} = 1.5 V, I _{NO} , I _{NC} = 100 mA	Room			0.6	
Switch Off Leakage Current	I _{NO(off),} I _{NC(off)}		Room Full	- 10 - 100		10 100	
	I _{COM(off)} V _{NO} , V _{NC} = 0.3 V / 4 V, V _{COM} = 4 V / 0.3 V	Room Full	- 10 - 100		10 100	nA	
Channel-On Leakage Current	I _{COM(on)}	$V+ = 4.3 \text{ V}, V_{NO}, V_{NC} = V_{COM} = 0.3 \text{ V} / 4 \text{ V}$	Room Full	- 10 - 100		10 100	
Digital Control							
Input High Voltage	V_{INH}		Full	1.4			V
Input Low Voltage	V_{INL}		Full			0.5	
Input Capacitance ^d	C _{in}		Full		7		pF
Input Current ^f	I _{INL} or I _{INH}	$V_{IN} = 0 \text{ V or V} +$	Full	- 1		1	μΑ
Dynamic Characteristics							
Turn-On Time	t _{ON}	V+ = 3.0 V, V _{NO} or V _{NC} = 1.5 V	Room Full		22	44 48	
Turn-Off Time	t _{OFF}	$R_L = 300 \Omega$, $C_L = 35 pF$ Figure 1 and 2	Room Full		8	29 30	ns
Break-Before-Make Time	t _d		Room	1			
Charge Injection ^d	Q_{INJ}	$C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN} = 0 \Omega, \text{ Figure 3}$	Room		28		рC
Off-Isolation ^d	O _{IRR}	$R_1 = 50 \Omega, C_1 = 5 pF, f = 1 MHz$	Room		- 54		dB
Crosstalk ^d	X _{TALK}	11 - 30 34 0[- 3 μι, ι = 1 ΙΝΙΙ ΙΖ	Room		- 57		
NO, NC Off Capacitance ^d	C _{NO(off)} , C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		76		pF
Channel-On Capacitance ^d	C _{ON}		Room		178		
Power Supply							
Power Supply Range	V+			1.6		4.3	V
Power Supply Current	l+	$V+ = 3.6 \text{ V}, V_{IN} = 0 \text{ or } V+$			0.01	1.0	μΑ

Notes

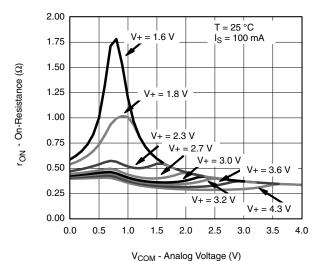
- a. Room = 25 °C, Full = as determined by the operating suffix.
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- c. Typical values are for design aid only, not guaranteed nor subject to production testing.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

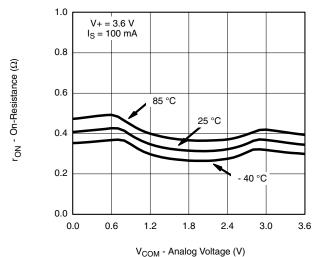
Vishay Siliconix

VISHAY.

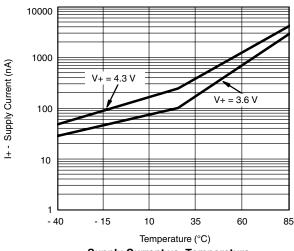
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



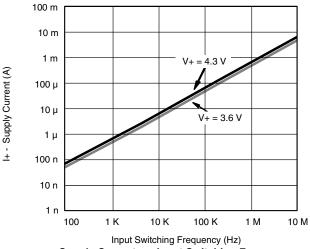
r_{ON} vs. V_{COM} and Single Supply Voltage



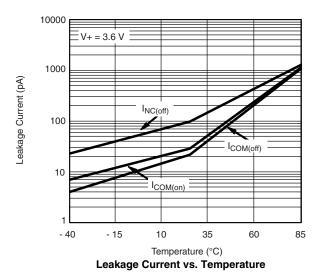
r_{ON} vs. Analog Voltage and Temperature

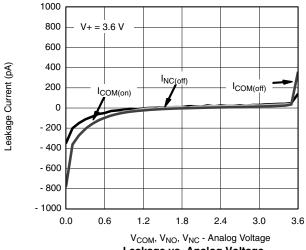


Supply Current vs. Temperature



Supply Current vs. Input Switching Frequency

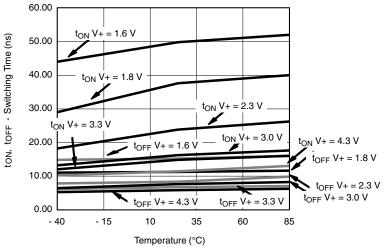




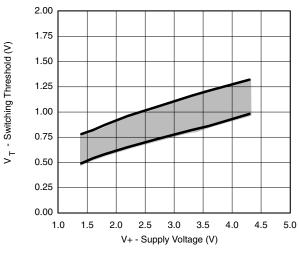
Leakage vs. Analog Voltage



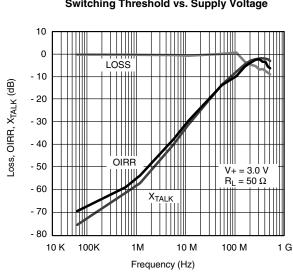
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



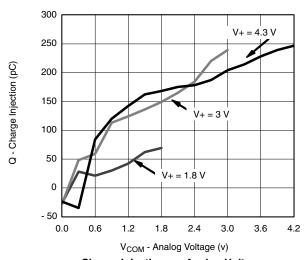
Switching Time vs. Temperature







Insertion Loss, Off-Isolation, Crosstalk vs. Frequency



Charge Injection vs. Analog Voltage

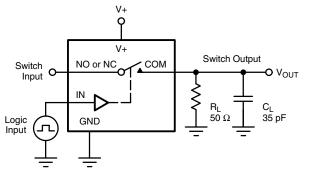
Vishay Siliconix

 $t_r < 5 \text{ ns}$

 $t_f < 5 \text{ ns}$

 $0.9 \times V_{OUT}$

TEST CIRCUITS



Switch Output 0 V

 t_{ON}

 V_{INH}

C_L (includes fixture and stray capacitance)

$$V_{OUT} = V_{COM} \left(\frac{R_L}{R_L + R_{ON}} \right)$$

Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

50 %

Figure 1. Switching Time

Logic Input

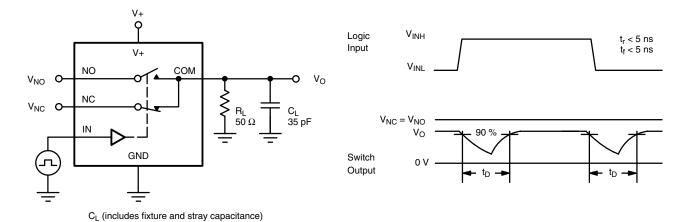
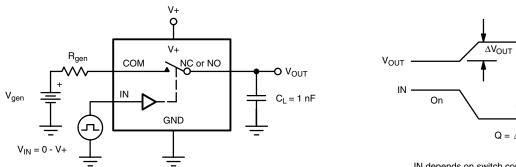


Figure 2. Break-Before-Make Interval



On $Q = \Delta V_{OUT} \times C_{L}$

IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection



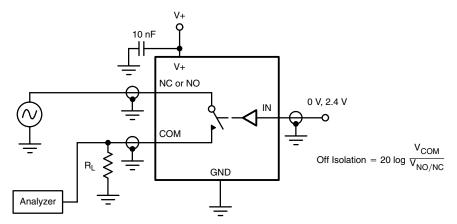


Figure 4. Off-Isolation

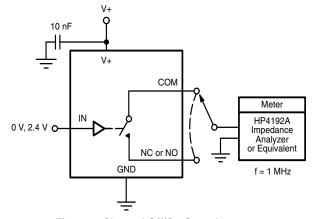


Figure 5. Channel Off/On Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?73538.



Vishay

Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.

Revision: 18-Jul-08

Document Number: 91000 www.vishay.com